

Data Sheet January 2000 File Number 3089.3

150A, 600V Hyperfast Diode

The RHRU15060 is a hyperfast diode with soft recovery characteristics (t_{rr} < 60ns). It has half the recovery time of ultrafast diodes and is of silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as a freewheeling/clamping diode and rectifier in a variety of switching power supplies and other power switching applications. Its low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits, thus reducing power loss in the switching transistors.

Formerly developmental type TA49071.

Ordering Information

PART NUMBER	PACKAGE	BRAND
RHRU15060	TO-218	RHRU15060

NOTE: When ordering, use the entire part number.

Symbol



Features

	Hyperfast with Soft Recovery<60ns
•	Operating Temperature
•	Reverse Voltage

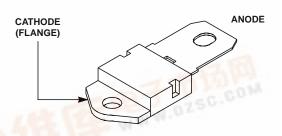
- Avalanche Energy Rated
- Planar Construction

Applications

- · Switching Power Supplies
- Power Switching Circuits
- General Purpose

Packaging

JEDEC STYLE TO-218



Absolute Maximum Ratings $T_C = 25^{\circ}C$

	RHRU15060	UNITS
Peak Repetitive Reverse VoltageVRRM	600	V
Working Peak Reverse Voltage	600	V
DC Blocking Voltage V _R	600	V
Average Rectified Forward Current	150	Α
$(T_C = 72^{\circ}C)$		
Repetitive Peak Surge Current	300	Α
(Square Wave, 20kHz)		
Nonrepetitive Peak Surge Current	1500	Α
(Halfwave, 1 Phase, 60Hz)		
Maximum Power Dissipation	375	W
Avalanche Energy (See Figures 7 and 8)	50	mJ
Operating and Storage Temperature	-65 to 175	°C



RHRU15060

Electrical Specifications $T_C = 25^{\circ}C$, Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
V _F	I _F = 150A	-	-	2.1	V
	I _F = 150A, T _C = 150 ^o C	-	-	1.6	V
I _R	V _R = 600V	-	-	250	μΑ
	V _R = 600V, T _C = 150 ^o C	-	-	2.0	mA
t _{rr}	I _F = 1A, dI _F /dt = 100A/μs	-	-	60	ns
	I _F = 150A, dI _F /dt = 100A/μs	-	-	70	ns
t _a	$I_F = 150A$, $dI_F/dt = 100A/\mu s$	-	43	-	ns
t _b	I _F = 150A, dI _F /dt = 100A/μs	-	20	-	ns
$R_{ heta JC}$		-	-	0.4	°C/W

DEFINITIONS

 V_F = Instantaneous forward voltage (pw = 300 μ s, D = 2%).

 I_R = Instantaneous reverse current.

 t_{rr} = Reverse recovery time (See Figure 6), summation of t_a + t_b .

t_a = Time to reach peak reverse current (See Figure 6).

 t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 6).

 $R_{\theta JC}$ = Thermal resistance junction to case.

pw = Pulse width.

D = Duty cycle.

Typical Performance Curves

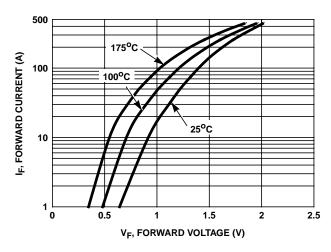


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

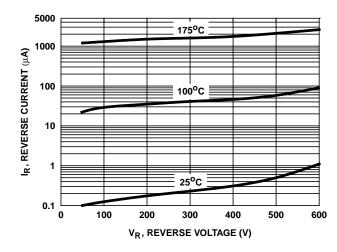


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

Typical Performance Curves (Continued)

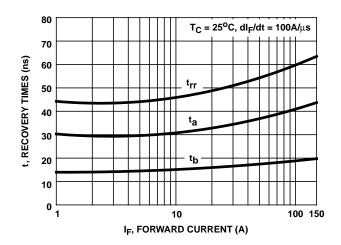


FIGURE 3. t_{rr}, t_a AND t_b CURVES vs FORWARD CURRENT

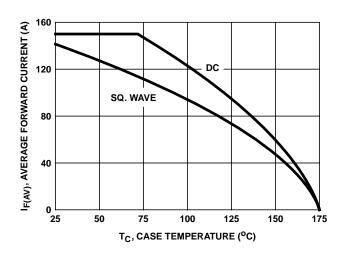


FIGURE 4. CURRENT DERATING CURVE

Test Circuits and Waveforms

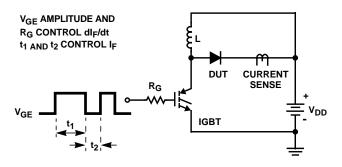


FIGURE 5. t_{rr} TEST CIRCUIT

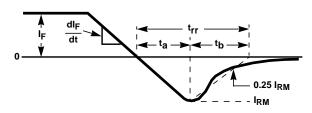


FIGURE 6. t_{rr} WAVEFORMS AND DEFINITIONS

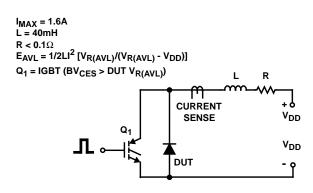


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT

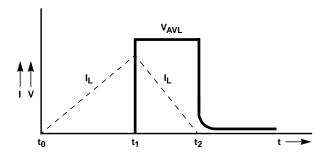


FIGURE 8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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